

橢圓形狀釔鈸錳氧微米線之磁阻研究

李致毅、王立民

E-mail: 9315035@mail.dyu.edu.tw

摘要

本論文之研究主要在探討橢圓形狀釔鈸錳氧微米線之形貌對磁阻之效應，我們已知釔鈸錳氧薄膜的金屬-絕緣體特性轉換溫度大於300 K，在室溫300 K時，有較佳的磁阻變化率。將釔鈸錳氧薄膜沉積在晶格匹配佳的鈦酸鈸單晶基板上，探討圓形與橢圓形形貌對釔鈸錳氧微米線磁阻特性之影響。此外，我們在鈦酸鈸基板上製作階梯晶界，再沉積釔鈸錳氧薄膜製作通過晶界的微米線，探討晶界在低溫低磁場的磁阻效應。經由PPMS (Physical Property Measurement System) 的量測，得知釔鈸錳氧微米線經過階梯晶界之後，有較大的磁阻變化率，經過分析應為穿隧效應之磁阻行為。最後，由一系列的量測，我們可發現到在居禮溫度以下時，磁阻隨外加磁場和溫度變化的特性分析，進而探討形貌效應對磁矩翻轉過程之影響。

關鍵詞：釔鈸錳氧；穿隧磁阻；階梯晶界

目錄

封面內頁 簽名頁 授權書	iii 中文摘要
iv 英文摘要	v 誌謝
vi 目錄	vii 圖目錄
x 表目錄	xiii 第
第一章 緒論 1.1 前言	1.1.2 磁阻特性之應用
1.2 1.3 研究目的	2 第二章 理論介紹 2.1 磁性之起源
5 2.2 磁區結構	9 2.3 磁阻與產生之機制
13 2.3.1 常磁阻	15 2.3.2 異向磁電阻
17 2.3.4 超巨磁阻	16 2.3.3 巨磁阻
19 2.3.6 自旋極化率之計算	17 2.3.5 穿隧磁阻
22 2.5 穿隧障壘之計算	20 2.4 RH圖形探討
離子蝕刻系統	24 第三章 實驗儀器介紹與原理 3.1 真空鍍膜系統與
25 3.2 黃光室微影製程	27 3.2.1 微影步驟
27 3.2.2 光阻簡介	30 3.3 電阻與磁阻之量測
32 3.4 原子力顯微鏡	33 3.5 磁化強度之量測
34 3.6 薄膜結構分析	36 第四章 實驗方法與步驟 4.1 實驗流程
37 4.2 SrTiO ₃ 基座上階梯之製作	38 4.2.1 階梯之微影製程
40 4.2.2 階梯之蝕刻	43 4.2.3 AFM檢測
43 4.3 LSMO之成長	45 4.3.1 薄膜平整度
膜厚量測	45 4.4 微米線之製作
48 第五章 結果與討論 5.1 磁化強度-溫度量測	48 4.5 量測
5.2 XRD量測	51 5.3 電阻率與溫度關係之分析
C-epi與E3-epi之電阻率-溫度之比較	52 5.3.1
53 5.3.2 E3-epi與E3-step之電阻率-溫度之比較	55 5.4 磁阻與外加磁場關係圖之探討
57 5.4.1 E3-epi與E3-step磁阻變化率-外加磁場關係之探討	60 5.5 穿隧磁阻對溫度關係之探討
63 第六章 結論	66 參考文獻
	67

參考文獻

1. S. Jin, T. H. Tiefel, M. M. Cormak, R. A. Fastnacht, R. Ramesh and L. H. Chen, Science 264, 413, 1994.
2. K. K. Chio and Y. Yamazaki, "Substrate-Dependent Micro-structure and Magnetoresistance of La-Sr-Mn-O Thin Films Grown by RF Sputtering", Jpn. J. Appl. Phys. Vol. 38, 1999, p. 56-60.
3. Young Suk Cho, "Magnetoresistance of La_{1-x}Sr_xMnO₃ films deposited by RF magnetron co-sputtering," Journal of Magnetism and Magnetic Materials 226-230, 2001, p.754-756.
4. K. Steenbeck, T. Eick, K. Kirsch, K. O'Donnell, "magnetoresistance of

La_{0.8}Sr_{0.2}MnO₃-single crystal films ", Appl. Phys. Lett. 71(7), 25 August, 1997, p. 968-970. 5. S. P. Isaac, N. D. Mathur, J. E. Evtts, and M. G. Blamire, " Magnetoresistance of artificial La_{0.7}Sr_{0.3}MnO₃ grain boundaries as a function of misorientation angle ", Applied Physics Letters Volume 72, Number 16, 20 April, 1998, p. 2038-2040. 6. Whiley, " Soshin Chikazumi,Physics of Ferromagnetism ", 1964, p. 3. 7. Charles Kittel, "Introduction to Solid State Physics 4th ed.", John Wiley & Sons, New York, 2000, Chap. 14-15, 1996. 8. B.D. Cullity, " Introduction to Magnetic Materials ", Addison-Wesley, Massachusetts, 1972, p. 85. 9. David J. Griffiths, " Introduction to Electrodynamics ", Academic Press, New York, 1989, p.245. 10.宛德福、馬興隆, " 磁性物理學 ", 電子工業出版社, 1999. 11.李景明, 張慶瑞, " 磁性技術手冊 ", 2000, 頁5. 12.陳立翰, " 磁性技術手冊 ", 2000, 頁425. 13.張慶瑞, " 中華民國磁性技術協會會訊 ", 第十九期, 1999, p. 5. 14. Robert C. O ' Handley, " Modern Magnetic Materials Principles and Applications ", John Wiley & Sons, New York, 2000. 15. Chien, C. L., and C. R. Westgate, eds. " The Hall Effect ", Plenum Press, New York, 1980. 16. C. Zener, Phys. Rev. 82 403, 1951. 17. M. Julliere, Phys. Lett. 54A, 225, 1975. 18. L. M. Wang, Chen-Chung Liu, H. C. Yang, H. E. Horng, " Effects of step-edge conditions on the magnetoresistance of LaSrMnO tunneling junctions ", Thin Solid Films 457, 2004, 359 364. 19. L. M. Wang, Chen-Chung Liu, H. C. Yang, H. E. Horng, " Room-temperature tunneling magnetoresistance in La_{0.7}Sr_{0.3}MnO₃ step-edge junctions ", J. Appl. Phys. Vol. 95, No. 9, 1 May, 2004. 20.許樹恩,吳泰伯, " X光繞射原理與材料結構分析 ", 中國材料科學學會, 1993, 頁121. 21. B. D. Cullity, " Elements of X-ray Diffraction ", Addison-Wesley, Massachusetts, 1977, p.81. 22. K. Char, M. S. Colclough, S. M. Garrison, N. Newman, and G. Zaharchuk, " Bi-epitaxial grain boundary junctions in YBa₂Cu₃O₇ ", Appl. Phys. Lett. 59, 733, 1991. 23. K. Char, M. S. Colclough, L. P. Lee, and G. Zaharchuk, " Extension of bi-epitaxial Josephson junction process to various substrates ", Appl. Phys. Lett., 59, 2177, 1991. 24. Yu. A. Boikov, A. L. Vasiliev, and T. Claeson, " Bi-epitaxial Josephson junctions with high current density based on YBa₂Cu₃O₇- films on silicon sapphire ", J. Appl. Phys. 77, 1654, 1995. 25. Kiejin Lee and Ienair Iguchi, " Josephson effects in YBaCuO grain boundary junctions on (100)MgO bicrystal substrates ", Appl. Phys. Lett. 66, 769, 1995. 26. I. V. Borisenko, P. B. Mozhaev, G. A. Ovsyannikov, K. Y. Constantinian, E. A. Stepantsov, " Superconducting current-phase relation in high-T_c symmetrical bicrystal junction ", Physica C 368, 328, 2002. 27. Gensoh Matsubara, Katsumi Eikyu, Masayuki Miyazaki, Hiroshi Kimura and Yoichi Okabe, " Fabrication of YBCO/PBCO/SrTiO₃/PBCO/YBCO Layered Structure for Superconductor-Insulator-Superconductor Tunnel-Type Josephson Junction ", Jpn. J. Appl. Phys. 32, L1324, 1993. 28. Toshiyuki Matsui, Takeshi Suzuki, Akihiko Ohi, Hiroshi Kimura, and Kazuo Mukae, " Fabrication of Tunnel Junctions with YBCO/Insulator/YBCO Layered Structure Using (013)-Oriented Films as Base Layer ", Jpn. J. Appl. Phys. 32, L1218, 1993. 29. L. C. Ku, H. M. Cho, J. H. Lu, S. Y. Wang, W. B. Jian, H. C. Yang, and H.E. Horng, " Characteristics of YBa₂Cu₃O_x step-edge Josephson junctions on MgO substrate ", Physica C 229, 320, 1994. 30.楊鴻昌, 物理專文 " 認識超導量子干涉元件SQUID ", 物理雙月刊11卷5期。 31.楊鴻昌, 超導 " 最敏感的感測元件SQUID及其前瞻性應用 ",物理雙月刊24卷5期。 32. L. M. Wang, H. C. Yang, and H. E. Horng, " Electrical transport and carrier density collapse in doped manganite thin films ", Phys. Rev. B, volume 64, 224 423. 33. X.W.Li, A.Gupta, G. Xiao, G.Q. Gong, Appl.Phys.Lett. 71, 1997, 1124. 34. K. Hamaya, T. Taniyama, Y. Y. amazaki, J. Appl. Phys. 89, 2001, 6320. 35. C. H. Shang, J. Nowak, R. Jansen, and J. S. Moodera, Phys. Rev. B 58, R2917, 1998. 36. J. B. Philipp, L. Alff, A. Marx, and R. Gross, Phys. Rev. B 66, 224417, 2002.